



A

AMENDMENT TRANSMITTAL LETTER

Docket No.
SON-1745

Application No.
09/512,336

Filing Date
February 24, 2000

Examiner
K. Chen

Art Unit
1765

Applicant(s): Seiichi FUKUDA

Invention: DRY ETCHING METHOD AND METHOD OF MANUFACTURING SEMICONDUCTOR APPARATUS

TO THE COMMISSIONER FOR PATENTS

Transmitted herewith is an amendment in the above-identified application.

The fee has been calculated and is transmitted as shown below.

CLAIMS AS AMENDED					
	Claims Remaining After Amendment	Highest Number Previously Paid	Number Extra Claims Present	Rate	
Total Claims	4	- 20 =		x	0.00
Independent Claims	2	- 3 =		x	0.00
Multiple Dependent Claims (check if applicable) <input type="checkbox"/>					
Other fee (please specify):					
TOTAL ADDITIONAL FEE FOR THIS AMENDMENT:					0.00

☒ Large Entity

☐ Small Entity

☒ No additional fee is required for this amendment.

☐ Please charge Deposit Account No. _____ in the amount of \$ _____.
A duplicate copy of this sheet is enclosed.

☐ A check in the amount of \$ _____ to cover the filing fee is enclosed.

☐ Payment by credit card. Form PTO-2038 is attached.

☒ The Commissioner is hereby authorized to charge and credit Deposit Account No. 18-0013 as described below. A duplicate copy of this sheet is enclosed.

☒ Credit any overpayment.

☒ Charge any additional filing or application processing fees required under 37 CFR 1.16 and 1.17.

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Dated: November 14, 2002

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SON-1745

BOX AF

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In the Patent Application of

Seiichi FUKUDA

Serial No. 09/512,336

Filed: February 24, 2000

For: DRY ETCHING METHOD AND
METHOD OF MANUFACTURING
SEMICONDUCTOR APPARATUS

Group Art Unit: 1765

Examiner: K. Chen

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SECOND AMENDMENT AFTER FINAL UNDER 37 C.F.R § 1.116

BOX AF

Commissioner for Patents
Washington, DC 20231

Sir:

This is a second amendment following the final Office Action dated July 9, 2002. Please amend the application as follows.

IN THE CLAIMS:

Please amend claims 1 and 4 as shown in the attached Appendix. A clean version of the claims is presented below.

1. (amended) A dry etching method comprising the step of:
dry-etching a formed film of tungsten in its entirety as
originally formed using only a single mixed gas including a
fluorine-containing gas that includes a compound having
fluorine and carbon in a molecule, chlorine or hydrogen
bromide, oxygen, and nitrogen,